## **Panasonic**

## DB3Y501KEL

## Silicon epitaxial planar type

For high speed switching circuits DB3X501K in NMini3 type package

#### ■ Features

- · Short reverse recovery time trr
- · Low terminal capacitance Ct
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol :4H

#### ■ Packaging

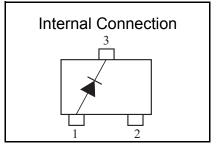
Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

### ■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Reverse voltage	VR	50	V
Repctitive peak reverse voltage	VRRM	50	V
Forward current (Average)	IF (AV)	200	mA
Peak forward current	IFM	300	mA
Non-repetitive peak forward surge current *1	IFSM	1	Α
Junction temperature	Tj	125	°C
Operating ambient temperature	Topr	-40 to +85	°C
Storage temperature	Tstg	-55 to +125	°C

Note) \*1 The peak-to-peak value in one cycle of 50 Hz sine wave (non-repetitive)

### Unit: mm 2.9 0.4 1.0 (0.95)(0.95)1.9 1. Anode 2. N.C. 3. Cathode Panasonic NMini3-R1-B **JEITA** SC-59A Code TO-236AA/SOT-23



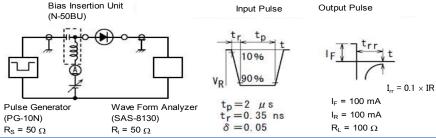
#### ■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Forward voltage	VF1	IF = 30 mA			0.36	V
	VF2	IF = 200 mA			0.55	V
Reverse current	IR	VR = 50 V			200	μΑ
Terminal capacitance	Ct	VR = 10 V, f = 1 MHz		4.0		pF
Reverse recovery time *1	ı trr	IF = IR = 100 mA, Irr = 0.1 $\times$ IR RL = 100 Ω		1.6		ns

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for Diodes.

- 2. This product is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.
- 3. Absolute frequency of input and output is 1000 MHz.

4. \*1 trr measurement circuit



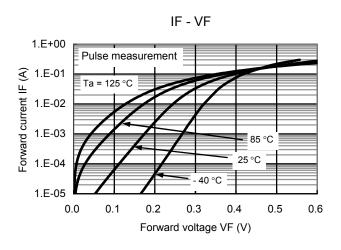
Page 1 of 3

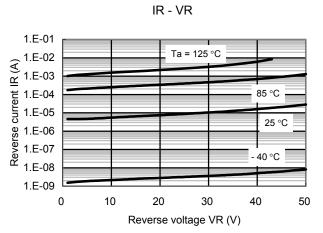
Established : 2013-04-27 Revised : ###-##-##

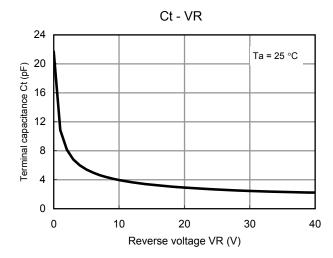
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Schottky Barrier Diode DB3Y501KEL

## Technical Data (reference)







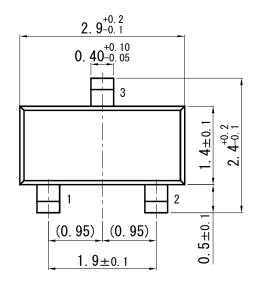
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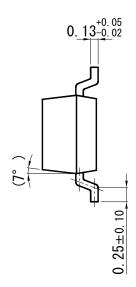
# **Panasonic**

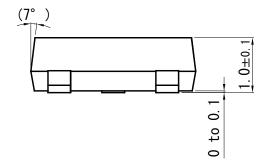
Schottky Barrier Diode DB3Y501KEL

NMini3-R1-B

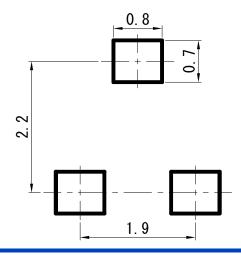








■ Land Pattern (Reference) (Unit : mm)



Established: 2013-04-27 Revised: ###-##-##

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